

## Supplementary Materials

# Industrial Silicon-Wafer-Wastage-Derived Carbon-Enfolded Si/Si-C/C Nanocomposite Anode Material through Plasma-Assisted Discharge Process for Rechargeable Li-Ion Storage

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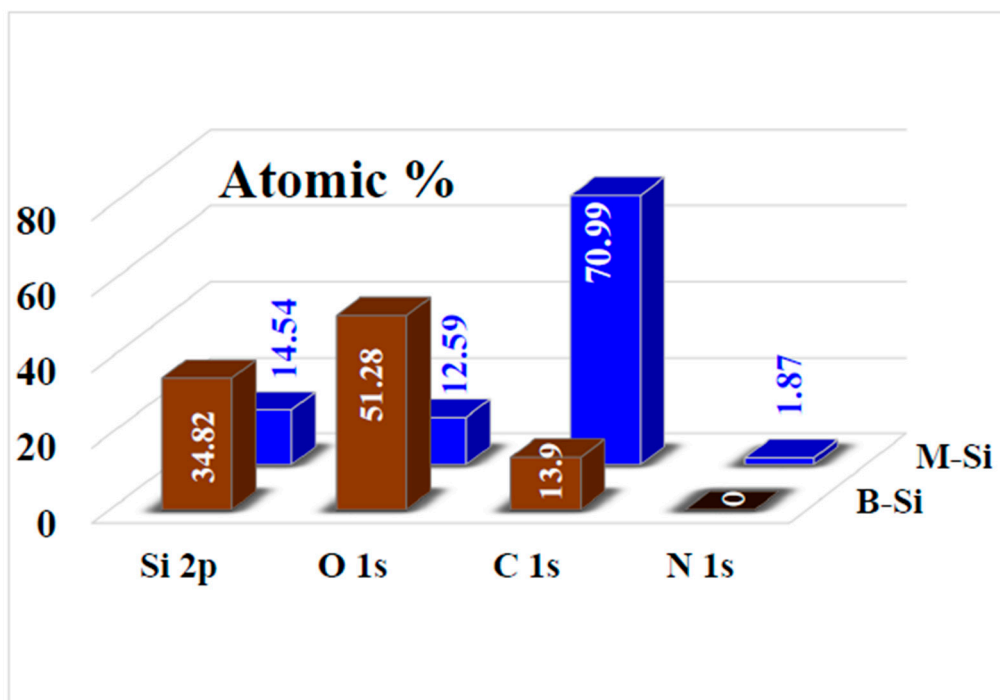
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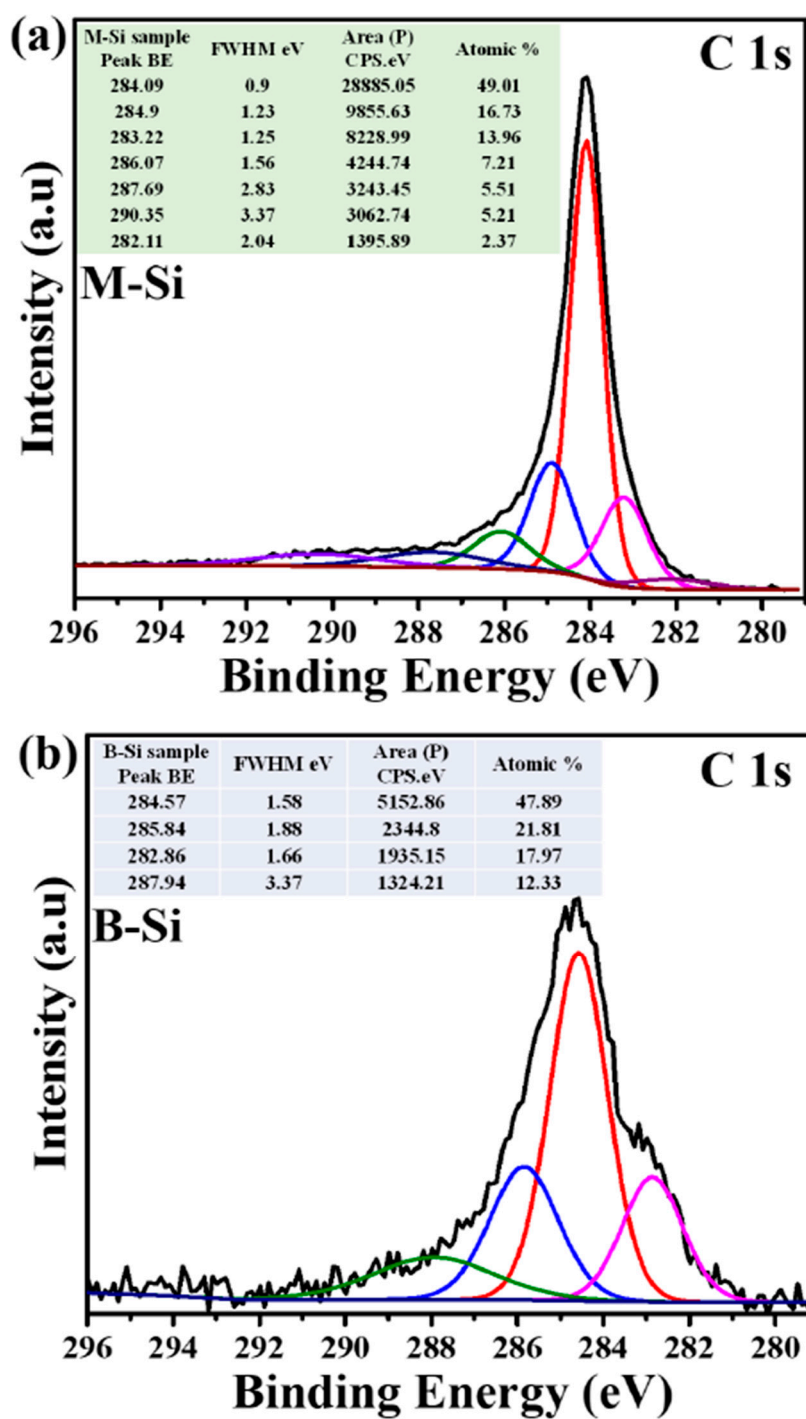
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## 1. Experimental physical and chemical characterization conditions

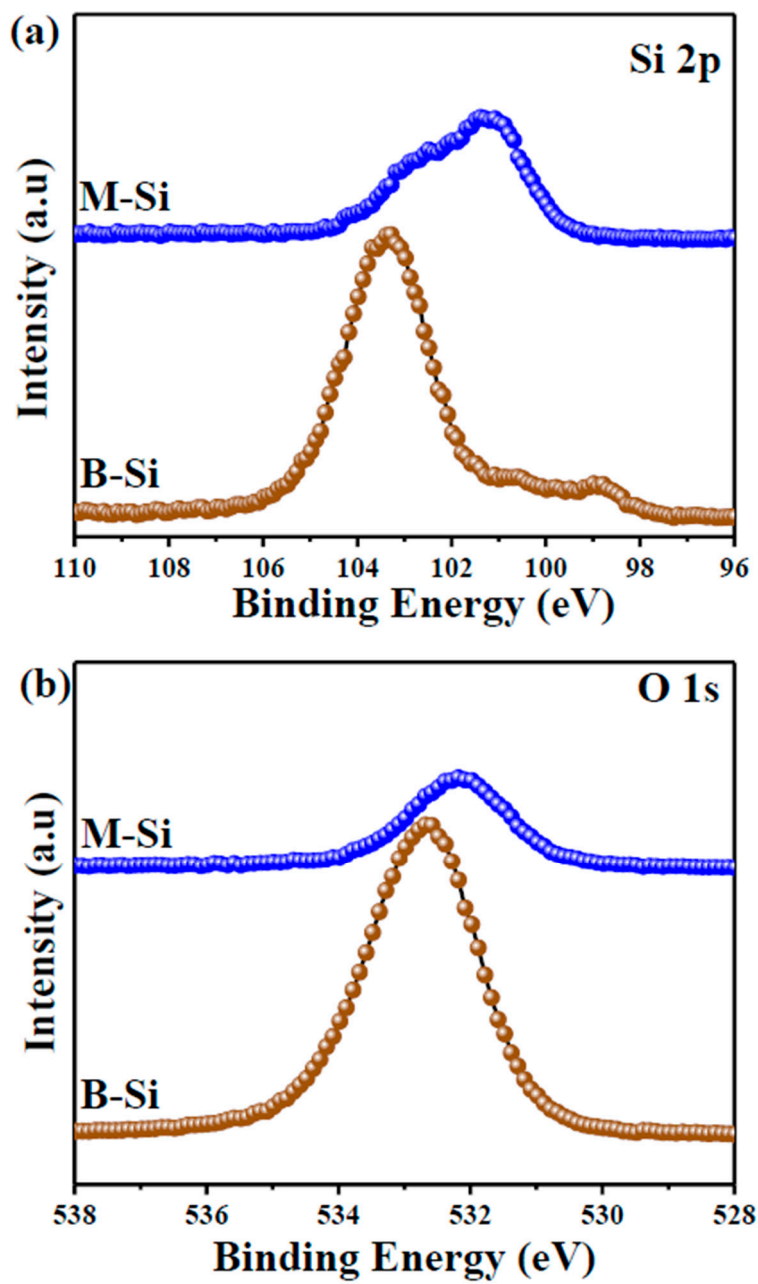
The crystal phase structure and purity were determined through X-ray powder diffraction (XRD) by using a Bruker D8 diffractometer with monochromatic  $\text{CuK}\alpha$  radiation. The diffractometer was operated at 40 kV and 20 mA with a wavelength ( $\lambda$ ) of 1.54060 Å. Diffraction data were recorded in a range  $2\theta = 10^\circ\text{--}80^\circ$ . The morphology of powders was investigated using a high-resolution transmission electron microscopic (HR-TEM, JEM2100). A Tristar 3000 was employed to accelerate the surface area, and a porosity instrument was used to measure the  $\text{N}_2$  adsorption/desorption isotherms of the prepared product.



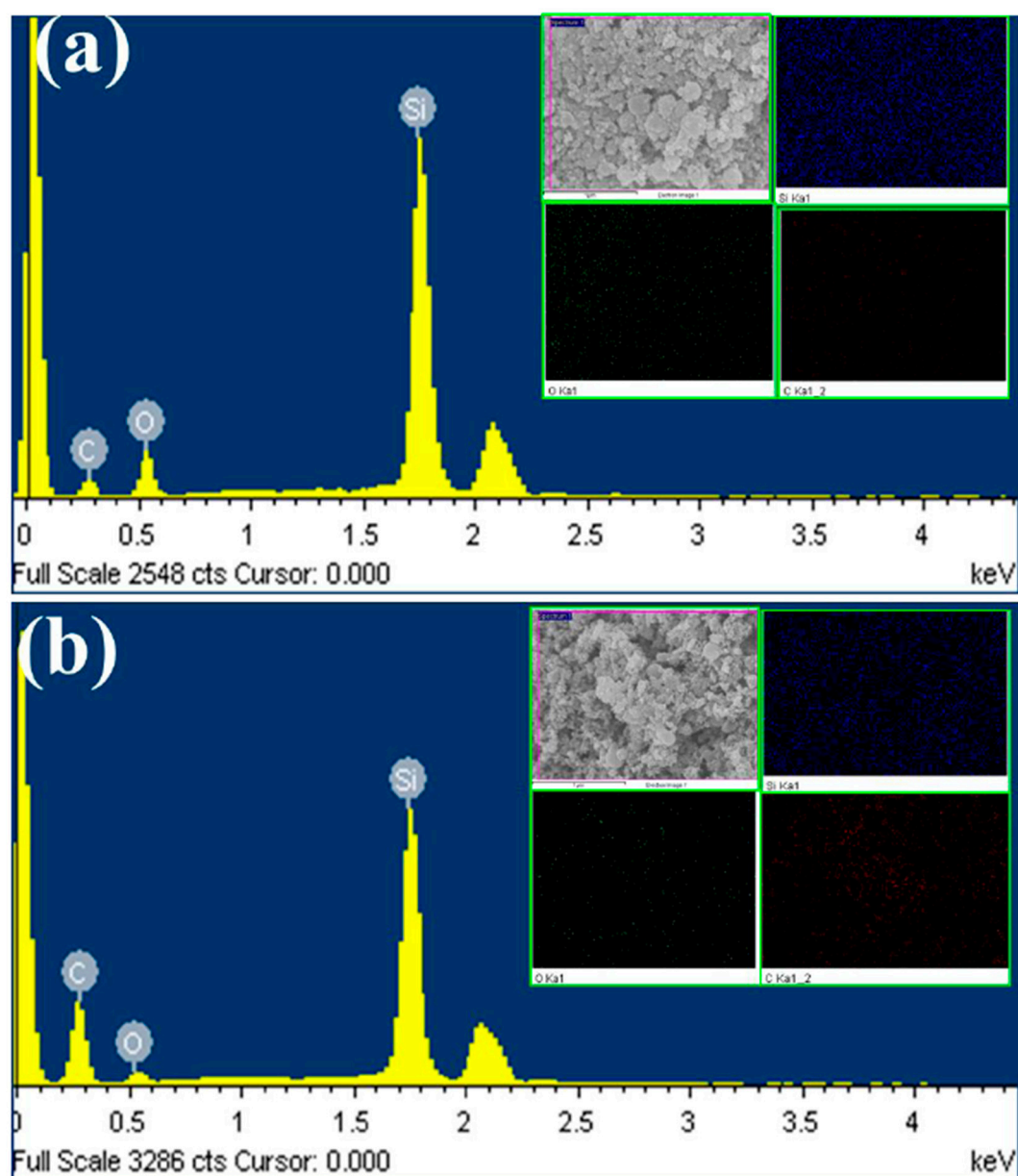
**Figure S1.** The M-Si and B-Si samples presence of elements atomic percentage estimated from XPS survey scan.



**Figure S2.** High-resolution C 1s XPS with deconvoluted fitted spectra of **(a)** M-Si and **(b)** B-Si samples, respectively.



**Figure S3.** High-resolution O 1s XPS of (a) M-Si and (b) B-Si samples.



**Figure S4.** FE-SEM coupled EDX spectra of **(a)** M-Si and **(b)** B-Si samples, inset the corresponding E-mapping images.